

# isc Silicon NPN Power Transistor

BDX24

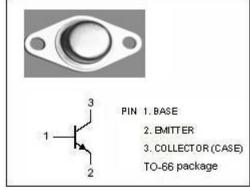
#### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub> = 40V (Min)
- · Excellent Safe Operating Area
- · Low Collector-Emitter Saturation Voltage
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.



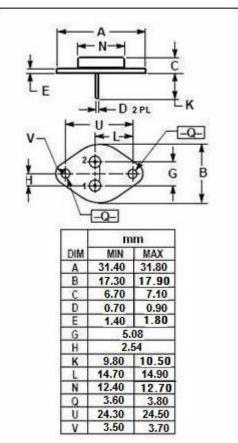
#### **APPLICATIONS**

Designed for general purpose switching and amplifier applications



# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	50	V
Vceo	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
Ic	Collector Current-Continuous 4		А
I <sub>B</sub>	Base Current-Continuous	2	А
Pc	Collector Power Dissipation@T <sub>C</sub> =25℃ 29		W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature -65~150		$^{\circ}$



## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	7.0	°C/W



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#### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	40		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.5A; I <sub>B</sub> = 50mA		1.0	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 1A		3.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	Ic= 0.5A; Vc== 4V		1.7	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 40V; I <sub>B</sub> = 0		0.5	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> =50V ; I <sub>E</sub> = 0		0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0		0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 4V	25	100	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	5		
fτ	Current Gain-Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V; f=1.0MHz	3		MHz

#### **NOTICE:**

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